Lecture-3

Photo-Diodes

Photo-generation:

> An important generation process in device operation is *photo-generation*

> If the photon energy (hv) is greater than the band gap energy, then the light will be absorbed and electron-hole pairs will be generated.



Photodetectors:



When light shines on a p-n junction, the photon energy RELEASES free electrons and holes i.e. electron-hole-pairs are generated optically.

They are referred to as PHOTO-ELECTRONS and PHOTO-HOLES

The applied voltage separates the photo-carriers attracting electrons toward "plus" and holes toward "minus"

As long as the light is ON, there is a current flowing through the p-n junction.

Photodiodes

Specifically designed for detector application and light penetration



Photodiodes

> Spectral response - an important characteristic of any photodetector. Measures how the photocurrent, I_L varies with the wavelength of incident light.

Frequency response - measures how rapidly the detector can respond to a time varying optical signal. The generated minority carriers have to diffuse to the depletion region before an electrical current can be observed externally. Since diffusion is a slow process, the maximum frequency response is a few tens of MHz for p n junctions.

➢ Higher frequency response (a few GHz) can be achieved using p-i-n diodes.

TUNNEL DIODE (Esaki Diode)

- It was introduced by Leo Esaki in 1958.
- Heavily-doped p-n junction
 - Impurity concentration is 1 part in 10³ as compared to 1 part in 10⁸ in p-n junction diode
- Width of the depletion layer is very small (about 100 A).
- It is generally made up of Ge and GaAs.
- It shows tunneling phenomenon.
- Circuit symbol of tunnel diode is :



What is Tunneling?

- Classically, carrier must have energy at least equal to potentialbarrier height to cross the junction.
- But according to Quantum mechanics there is finite probability that it can penetrate through the barrier for a thin width.
- This phenomenon is
 called tunneling and
 hence the Esaki Diode
 is know as
 Tunnel Diode.



Triangular potential barrier approximation of the potential barrier in the tunnel diode.

Metal Contacts



<Ohmic contact>

- No rectifying action.
- The current can flow in both direction

<Schottky contact>

- The difference of carrier concentrations of the two materials at the contact.
- A barrier potential exists.
- rectifying action occurs.
- Mostly used in switching circuits. (turn on/off switches)

Metal Contacts I-V Characteristics

